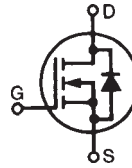


PolarHV™ Power MOSFET

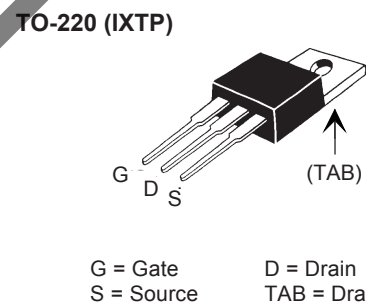
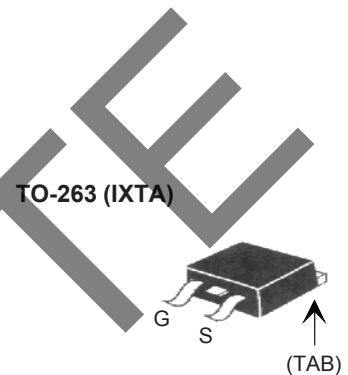
IXTA 6N50P
IXTP 6N50P

$V_{DSS} = 500 \text{ V}$
 $I_{D25} = 6 \text{ A}$
 $R_{DS(on)} \leq 1.1 \ \Omega$

N-Channel Enhancement Mode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	6	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	15	A
I_{AR}	$T_C = 25^\circ\text{C}$	6	A
E_{AR}	$T_C = 25^\circ\text{C}$	20	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	250	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 18 \ \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13/10 Nm/lb.in.	
Weight	TO-220	4	g
	TO-263	3	g



Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \ \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 50 \ \mu\text{A}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			50 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \ \mu\text{s}$, duty cycle $d \leq 2 \%$			1.1 Ω

Features

- † International standard packages
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

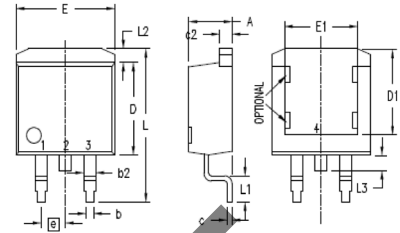
Advantages

- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$, pulse test	3.5	5.5	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		740	pF
C_{oss}			85	pF
C_{rss}			8	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 18\ \Omega$ (External)		26	ns
t_r			28	ns
$t_{d(off)}$			65	ns
t_f			26	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		14.6	nC
Q_{gs}			4.8	nC
Q_{gd}			5.6	nC
R_{thJC}				1.25°C/W
R_{thCS}	(TO-220)	0.25		$^\circ\text{C/W}$

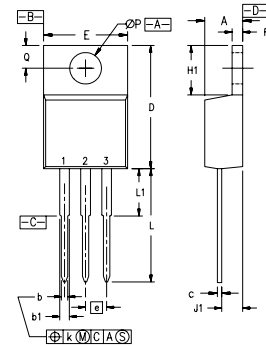
Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{ V}$			6 A
I_{SM}	Repetitive			18 A
V_{SD}	$I_F = I_s, V_{GS} = 0\text{ V}, -di/dt = 100\text{ A}/\mu\text{s}$			1.5 V
t_{rr}	Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$	400		ns

TO-263 (IXTA) Outline


1. GATE
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR) BOTTOM SIDE

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXTP) Outline


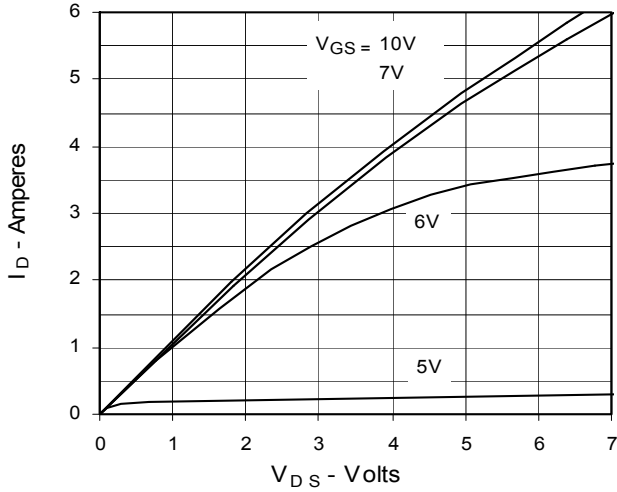
- Pins: 1 - Gate 2 - Drain
 3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

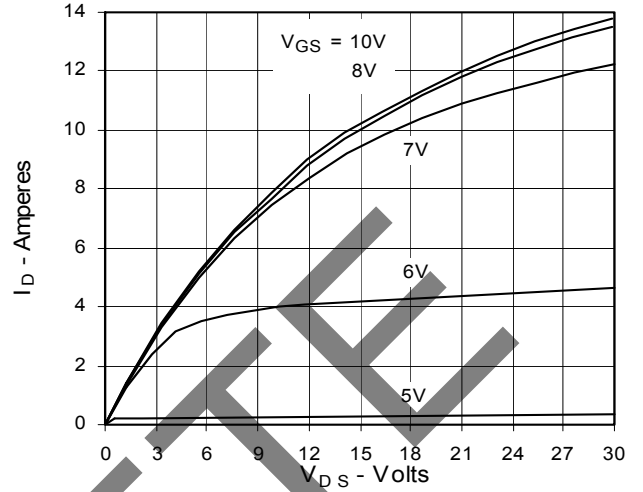
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

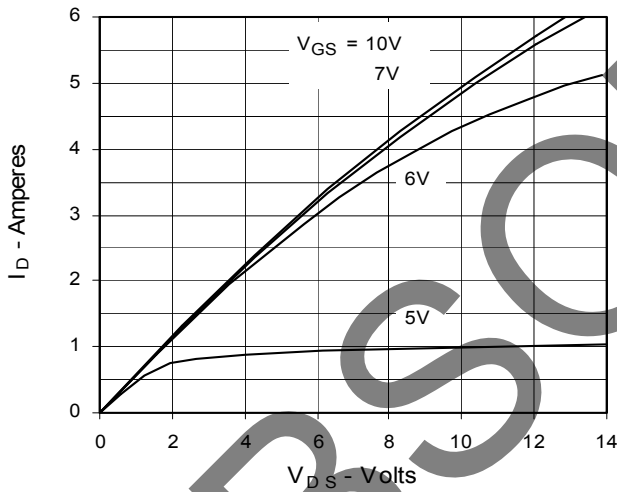
**Fig. 1. Output Characteristics
@ 25°C**



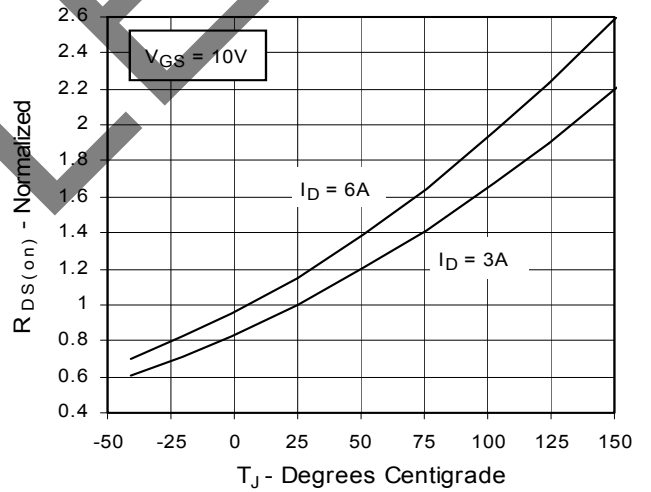
**Fig. 2. Extended Output Characteristics
@ 25°C**



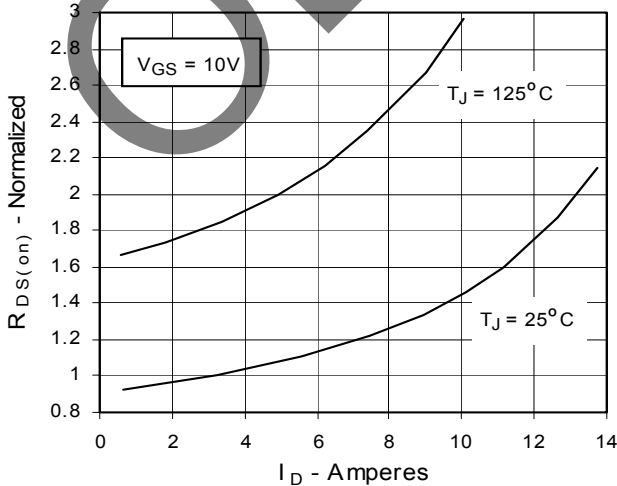
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

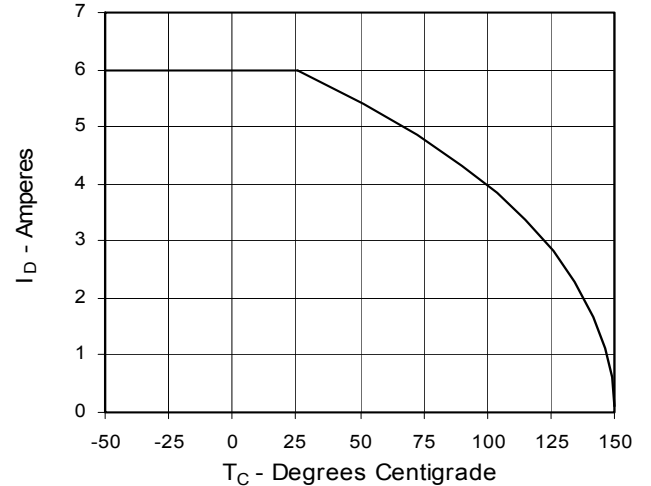


Fig. 7. Input Admittance

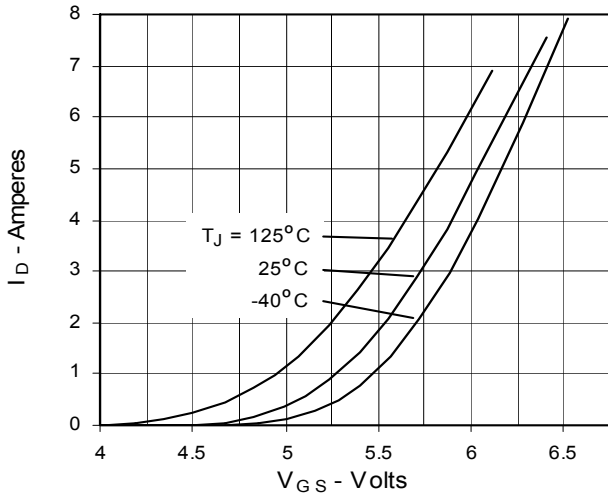


Fig. 8. Transconductance

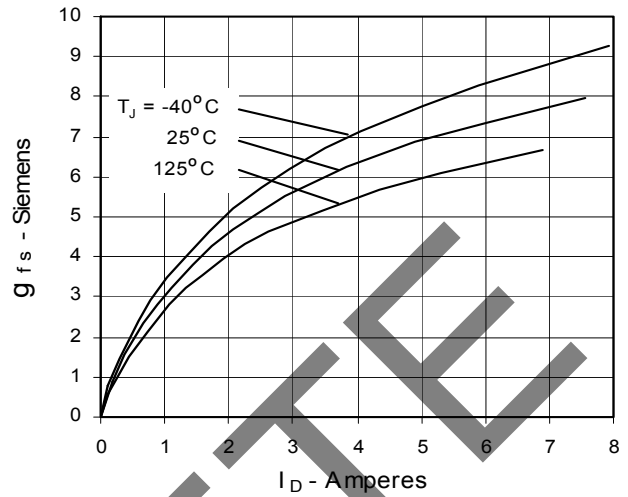


Fig. 9. Source Current vs. Source-To-Drain Voltage

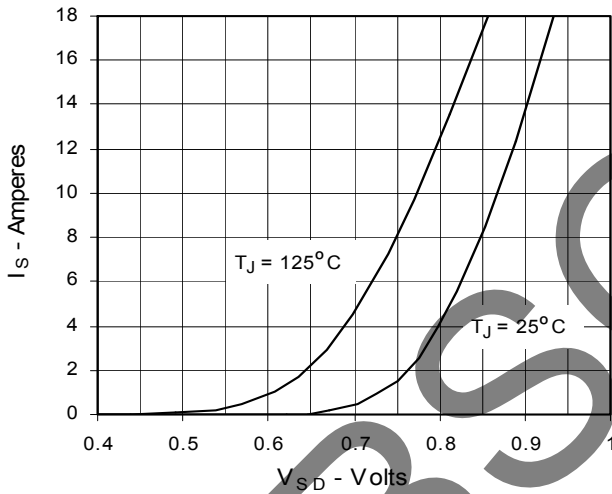


Fig. 10. Gate Charge

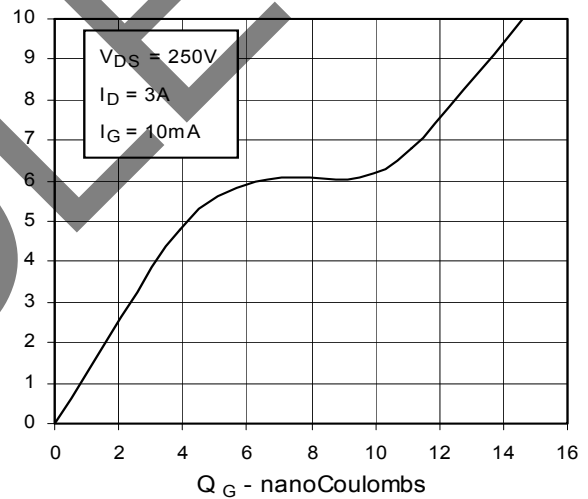


Fig. 11. Capacitance

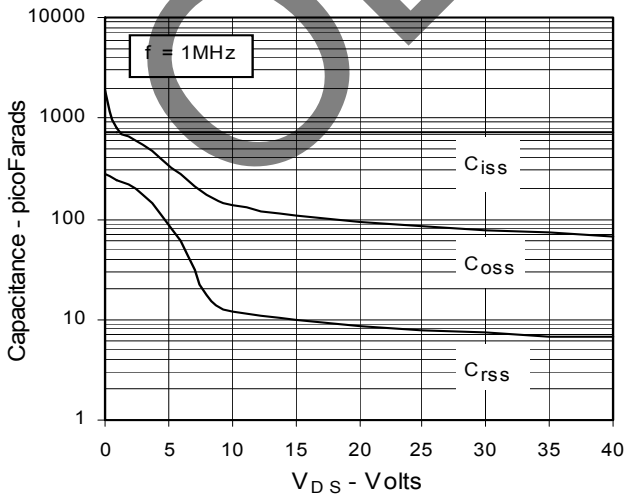


Fig. 12. Forward-Bias Safe Operating Area

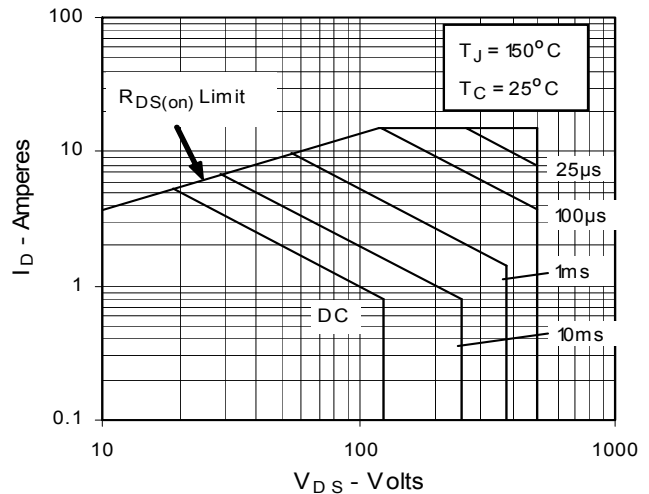
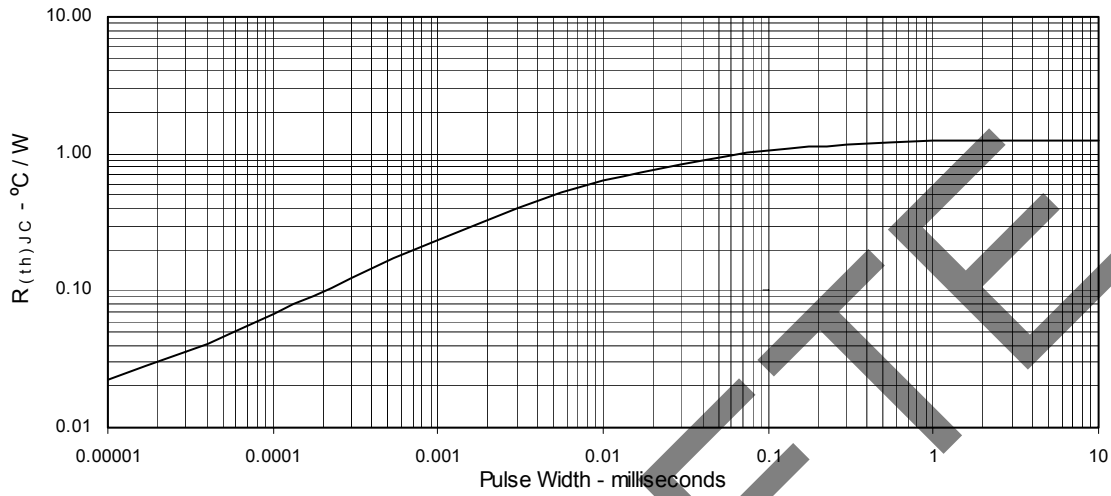


Fig. 13. Maximum Transient Thermal Resistance



OBSOLETE



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